

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1	10/516,417	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/09/14 15:35
L2	1	((first adj pad) with (first adj potential)) and ((second adj pad) with (second adj potential)) and ((third adj pad) with (third adj potential)) and ((fourth adj pad) with (fourth adj potential)).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/09/14 16:08
L3	582	(first adj transistor) same ((first adj potential) same (second adj potential))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/09/14 16:08
L4	44	(second adj transistor) same ((third adj potential) same (fourth adj potential))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/09/14 16:08
L5	29	L3 and L4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/09/14 16:08
L6	16	@ad <= "20030516" and L5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/09/14 16:08
L7	8357	((257/666) or (257/670) or (257/672) or (257/673) or (257/690) or (257/734) or (257/779) or (257/780) or (257/781) or (257/784) or (257/694) or (257/695) or (257/ E23.042) or (257/	USPAT	OR	OFF	2008/09/14 16:09

		E33.066) or (257/ E23.01) or (257/ E23.011)).CCLS.				
L11	8357	((257/666) or (257/670) or (257/672) or (257/673) or (257/690) or (257/734) or (257/779) or (257/780) or (257/781) or (257/784) or (257/694) or (257/695) or (257/ E23.042) or (257/ E33.066) or (257/ E23.01) or (257/ E23.011)).CCLS.	USPAT	OR	OFF	2008/09/14 16:09
L12	15	L11 and (transistor or "MOSFET" or "FET" or "TFT" or (integrated adj circuit) or (semiconductor adj device) or chip or die) same (first adj (potential or voltage or ground)) same (second adj (potential or voltage or ground)) same (pad or contact) same (inner-lead\$2 or lead\$2 or leadframe\$2 or finger\$2 or ring\$2)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/09/14 16:09
L13	11	@ad <= "20030516" and L12	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/09/14 16:09
S1	2831	(first adj transistor) with potential with (pad or contact or electrode)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/12 23:33
S2	3122	(second adj transistor) with potential with (pad or contact or electrode)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/12 23:33

S3	2331	S1 and S2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/12 23:34
S4	1119	S3 and @ad <= "20030516"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/12 23:34
S5	335	S4 and (first adj (pad or contact or electrode))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/12 23:35
S6	14	S4 and (fourth adj (pad or contact or electrode))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/12 23:35
S7	23	S4 and (first adj (pad or contact))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/13 00:03
S8	21	S4 and (second adj (pad or contact))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/13 00:03
S9	19	S7 and (second adj (pad or contact))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/13 00:03
S10	15	S7 and (third adj (pad or contact))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/13 00:03
S11	14	S9 and (third adj (pad or contact))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/13 00:03
S12	6	S11 and (fourth adj (pad or contact))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/13 00:04

S13	6	@ad <= "20030516" and S12	US_PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/13 00:04
S14	577	(first adj transistor) same ((first adj potential) same (second adj potential))	US_PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/13 00:10
S15	43	(second adj transistor) same ((third adj potential) same (fourth adj potential))	US_PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/13 00:10
S16	29	S14 and S15	US_PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/13 00:10
S17	16	@ad <= "20030516" and S16	US_PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/13 00:11
S18	76837	(first adj (transistor or "MOSFET" or "FET" or "TFT" or (integrated adj circuit) or (semiconductor adj device) or chip or die)) same ((first adj potential) same (second adj potential)) same (first adj (pad or contact)) or (second adj (pad or contact))	US_PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/13 00:45
S19	6702	(second adj (transistor or "MOSFET" or "FET" or "TFT" or (integrated adj circuit) or (semiconductor adj device) or chip or die)) same ((third adj potential) same (fourth adj potential)) same (third adj (pad or contact)) or (fourth adj (pad or contact))	US_PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/13 00:47

S20	5248	S18 and S19	US_PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/13 00:47
S21	5	(first adj (pad or contact)) same (inner adj lead) same (second adj (pad or contact)) same ((bus adj bar) or bus-bar)	US_PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/13 00:54
S22	1	S20 and S21	US_PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/13 00:54
S23	1	@ad <= "20030516" and S22	US_PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/13 00:56
S24	76837	(first adj (transistor or "MOSFET" or "FET" or "TFT" or (integrated adj circuit) or (semiconductor adj device) or chip or die)) same ((first adj potential) same (second adj potential)) same (first adj (pad or contact)) or (second adj (pad or contact))	US_PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/13 13:51
S25	6702	(second adj (transistor or "MOSFET" or "FET" or "TFT" or (integrated adj circuit) or (semiconductor adj device) or chip or die)) same ((third adj potential) same (fourth adj potential)) same (third adj (pad or contact)) or (fourth adj (pad or contact))	US_PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/13 13:52
S26	5248	S24 and S25	US_PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/13 13:52

S27	2478	@ad <= "20030516" and S26	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/13 13:52
S28	1	S27 and (pad or contact) and (inner adj lead) and ((bus adj bar) or bus-bar)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/13 13:53
S29	954	S27 and (pad or contact) and ((inner adj lead\$3) or lead\$2 or finger\$2 or bus-bar \$2 or (bus adj bar))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/13 13:57
S30	4336	(first adj (transistor or "MOSFET" or "FET" or "TFT" or (integrated adj circuit) or (semiconductor adj device) or chip or die)) with (wire or wiring)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/13 14:03
S31	15	S30 and S29	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/13 14:04
S32	4199	(second adj (transistor or "MOSFET" or "FET" or "TFT" or (integrated adj circuit) or (semiconductor adj device) or chip or die)) with (wire or wiring)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/13 14:14
S33	3144	S30 and S32	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/13 14:14
S34	347816	((pad or contact) with ((inner adj lead) or (bus adj bar) or bus-bar or lead or finger \$2))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/13 14:15
S35	858	S33 and S34	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/13 14:16

S36	389	@ad <= "20030516" and S35	US_PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/13 14:16
S37	17	("20010017411" "20020011654" "20020024146" "5359227" "5468999" "5691568" "5796171" "5801450" "5962926" "6121690" "6148505" "6160313" "6169331" "6215182" "6291898" "6297078" "6307271").PN.	US_PGPUB; USPAT; USOCR	OR	OFF	2008/07/13 15:18
S38	8233	((257/666) or (257/670) or (257/672) or (257/673) or (257/690) or (257/734) or (257/779) or (257/780) or (257/781) or (257/784) or (257/694) or (257/695) or (257/ E23.042) or (257/ E33.066) or (257/ E23.01) or (257/ E23.011)).CCLS.	USPAT	OR	OFF	2008/07/13 16:22
S39	15	S38 and (transistor or "MOSFET" or "FET" or "TFT" or (integrated adj circuit) or (semiconductor adj device) or chip or die) same (first adj (potential or voltage or ground)) same (second adj (potential or voltage or ground)) same (pad or contact) same (inner-lead\$2 or lead\$2 or leadframe\$2 or finger\$2 or ring\$2)	US_PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/13 16:28
S40	11	@ad <= "20030516" and S39	US_PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/13 16:28

S41	4837	((257/666) or (257/670) or (257/672) or (257/673) or (257/690) or (257/734) or (257/779) or (257/780) or (257/781) or (257/784) or (257/694) or (257/695) or (257/ E23.042) or (257/ E33.066) or (257/ E23.01) or (257/ E23.011)).CCLS.	US_PGPUB	OR	OFF	2008/07/13 16:30
S42	9	S41 and (transistor or "MOSFET" or "FET" or "TFT" or (integrated adj circuit) or (semiconductor adj device) or chip or die) same (first adj (potential or voltage or ground)) same (second adj (potential or voltage or ground)) same (pad or contact) same (inner-lead\$2 or lead\$2 or leadframe\$2 or finger\$2 or ring\$2)	US_PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/13 16:30
S43	4	@ad <= "20030516" and S42	US_PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/13 16:31
S44	1	((first adj pad) with (first adj potential)) and ((second adj pad) with (second adj potential)) and ((third adj pad) with (third adj potential)) and ((fourth adj pad) with (fourth adj potential)).clm.	US_PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/14 19:52

9/14/08 4:36:51 PM

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